



SEMITOP® 2

## IGBT Module

SK75GAL12T4

SK75GAR12T4

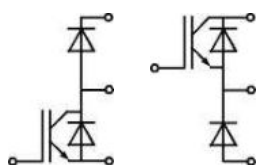
## Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

## Typical Applications\*

## Remarks

- $V_{CE,sat}$ ,  $V_F$  = chip level value



GAL

GAR

Absolute Maximum Ratings			T <sub>s</sub> = 25 °C, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		1200	V
I <sub>C</sub>	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	80	A
		T <sub>s</sub> = 70 °C	65	A
I <sub>CRM</sub>	I <sub>CRM</sub> = 3 x I <sub>Cnom</sub>		225	A
V <sub>GES</sub>			± 20	V
t <sub>psc</sub>	V <sub>CC</sub> = 800 V; V <sub>GE</sub> ≤ 15 V; T <sub>j</sub> = 150 °C V <sub>CES</sub> < 1200 V		10	µs
Inverse Diode				
I <sub>F</sub>	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	20	A
		T <sub>s</sub> = 70 °C	16	A
I <sub>FRM</sub>	I <sub>FRM</sub> = 3 x I <sub>Fnom</sub>		45	A
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave T <sub>j</sub> = 150 °C		90	A
Freewheeling Diode				
I <sub>F</sub>	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	70	A
		T <sub>s</sub> = 70 °C	55	A
I <sub>FRM</sub>	I <sub>FRM</sub> = 3xI <sub>Fnom</sub>		225	A
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave T <sub>j</sub> = 150 °C		425	A
Module				
I <sub>t(RMS)</sub>				A
T <sub>vj</sub>			-40 ... +175	°C
T <sub>stg</sub>			-40 ... +125	°C
V <sub>isol</sub>	AC, 1 min.		2500	V

Characteristics			T <sub>s</sub> = 25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V <sub>GE(th)</sub>	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 3 mA		5	5,8	6,5	V	
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = V <sub>CES</sub>		T <sub>j</sub> = 25 °C		1,0	mA	
			T <sub>j</sub> = 150 °C			mA	
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 20 V		T <sub>j</sub> = 25 °C		600	nA	
			T <sub>j</sub> = 150 °C			nA	
V <sub>CE0</sub>			T <sub>j</sub> = 25 °C		1,1	1,3	V
			T <sub>j</sub> = 150 °C		1	1,2	V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V		T <sub>j</sub> = 25°C		10		mΩ
			T <sub>j</sub> = 150°C		16		mΩ
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 75 A, V <sub>GE</sub> = 15 V		T <sub>j</sub> = 25°C <sub>chiplev.</sub>		1,85	2,05	V
			T <sub>j</sub> = 150°C <sub>chiplev.</sub>		2,25	2,45	V
C <sub>ies</sub>	V <sub>CE</sub> = 25, V <sub>GE</sub> = 0 V		f = 1 MHz		4,4		nF
C <sub>oes</sub>					0,29		nF
C <sub>res</sub>					0,235		nF
Q <sub>G</sub>	V <sub>GE</sub> =-7V...+15V				570		nC
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C				10		Ω
t <sub>d(on)</sub>	R <sub>Gon</sub> = 15 Ω di/dt = 2000 A/μs		V <sub>CC</sub> = 600V I <sub>C</sub> = 75A T <sub>j</sub> = 150 °C V <sub>GE</sub> = -7/+15V		50		ns
t <sub>r</sub>					60		ns
E <sub>on</sub>					13		mJ
t <sub>d(off)</sub>	R <sub>Goff</sub> = 15 Ω				500		ns
t <sub>f</sub>					60		ns
E <sub>off</sub>					7		mJ
R <sub>th(i-s)</sub>	per IGBT				0,74		K/W

# SK75GAL12T4



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## IGBT Module

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**SK75GAR12T4**

### Features

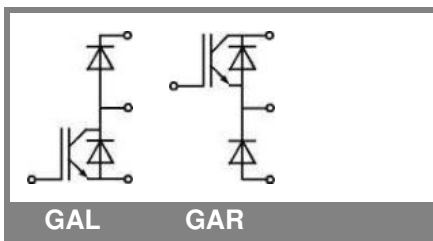
- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

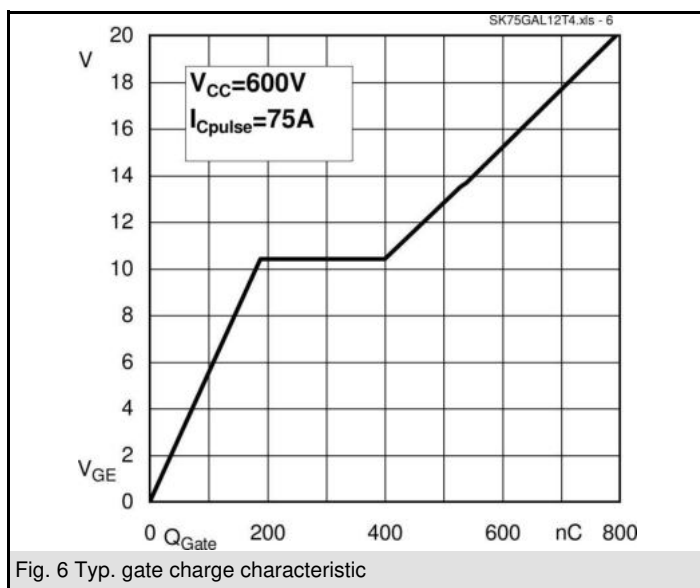
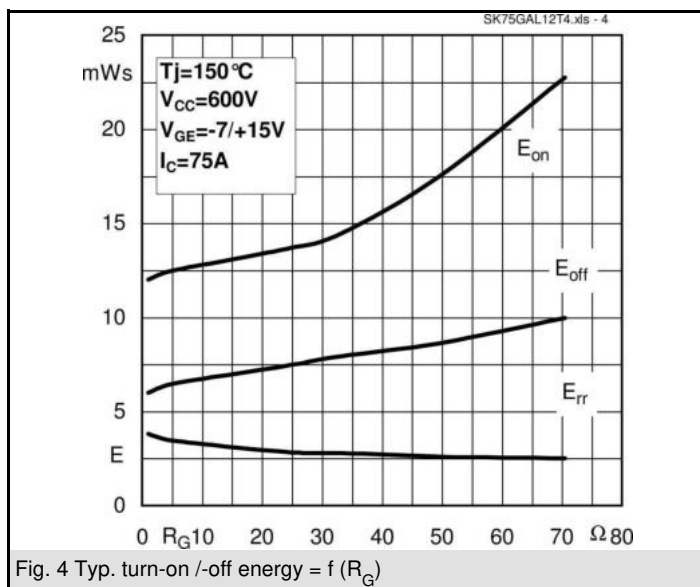
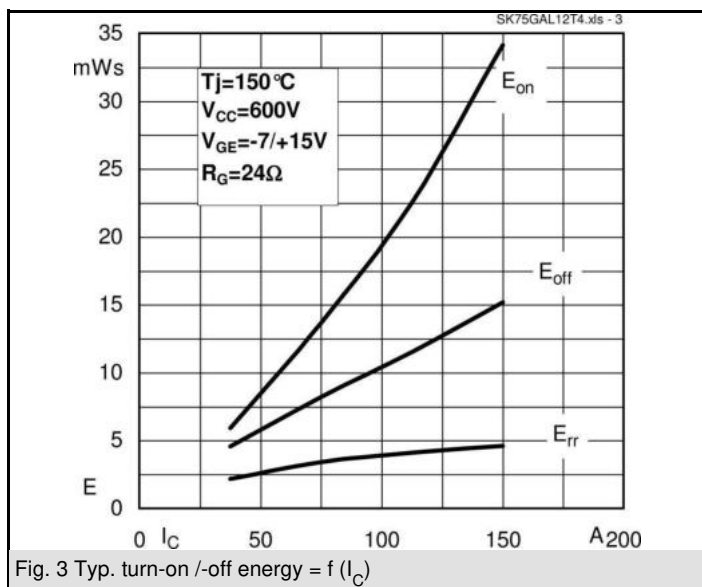
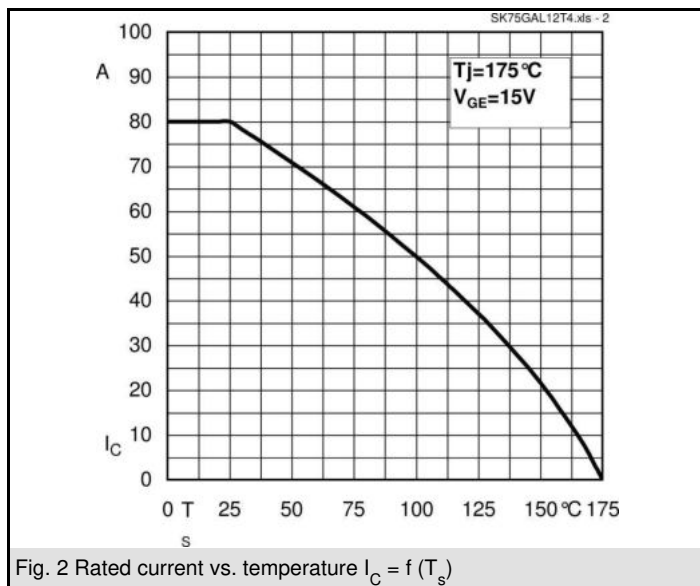
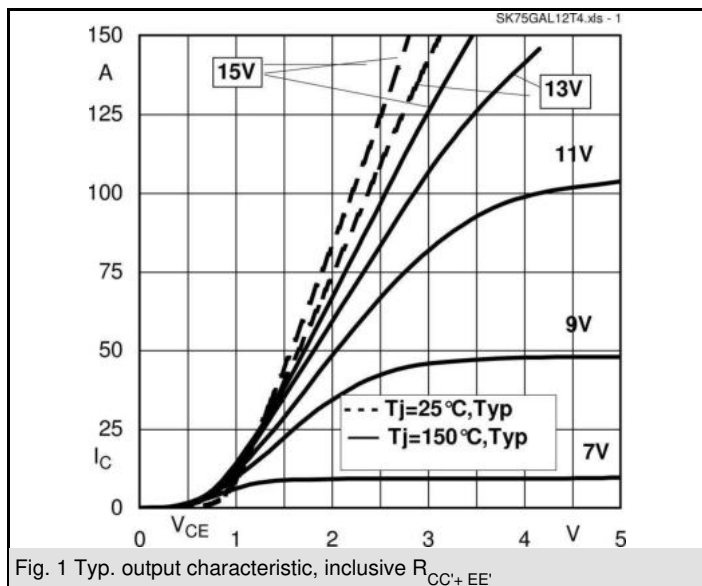
### Typical Applications\*

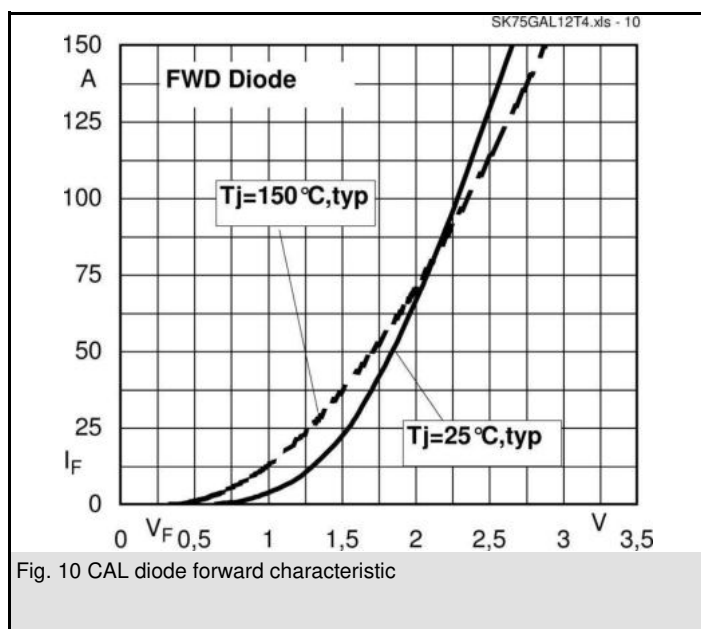
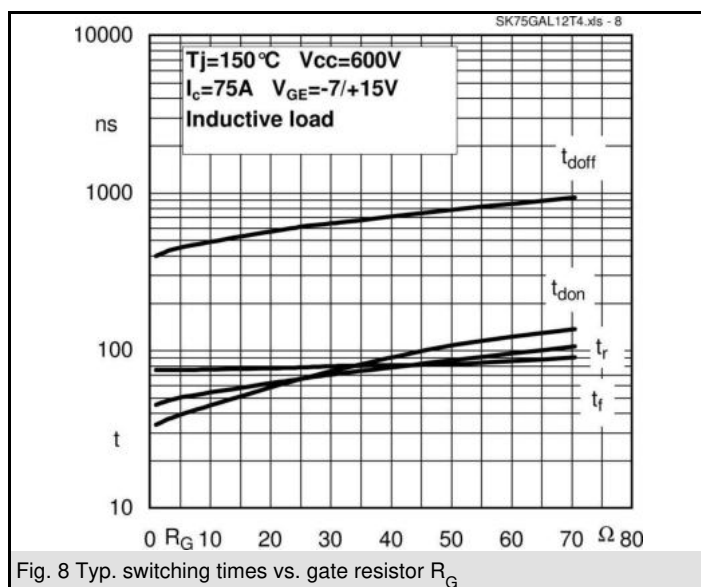
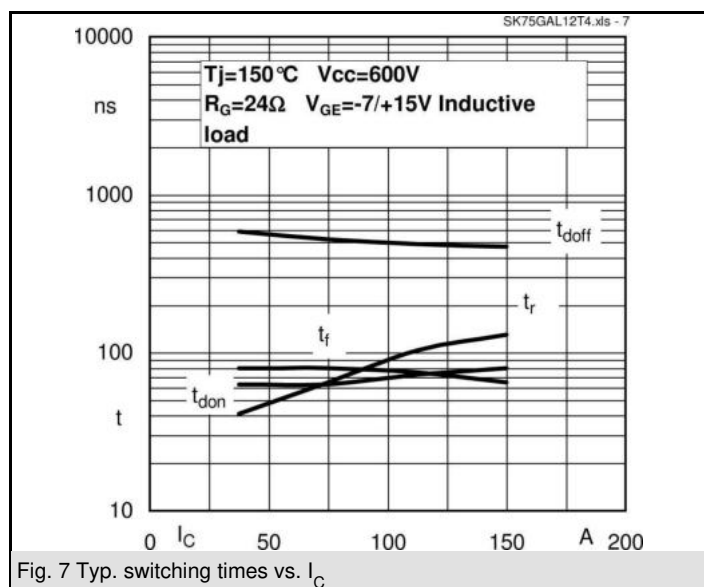
### Remarks

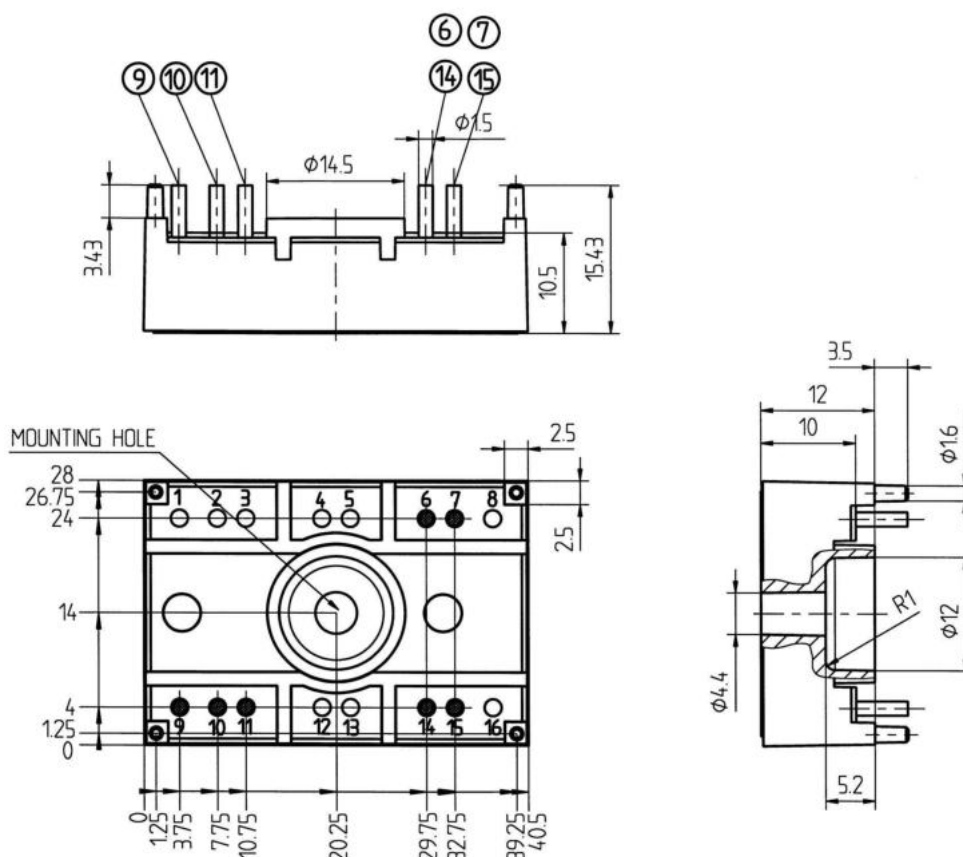
- $V_{CE,sat}$ ,  $V_F$  = chip level value

Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V <sub>F</sub> = V <sub>EC</sub>	I <sub>Fnom</sub> = 15 A; V <sub>GE</sub> = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		2,38	2,71	V
		T <sub>j</sub> = 150 °C <sub>chiplev.</sub>		2,44	2,77	V
V <sub>F0</sub>		T <sub>j</sub> = 25 °C		1,3	1,5	V
		T <sub>j</sub> = 150 °C		0,9	1,1	V
r <sub>F</sub>		T <sub>j</sub> = 25 °C		72	80,7	mΩ
		T <sub>j</sub> = 150 °C		102,8	111,6	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = A	T <sub>j</sub> = 150 °C				A
Q <sub>rr</sub>						μC
E <sub>rr</sub>	V <sub>CC</sub> = 600V					mJ
R <sub>th(j-s)D</sub>	per diode			2,34		K/W
Freewheeling Diode						
V <sub>F</sub> = V <sub>EC</sub>	I <sub>Fnom</sub> = 75 A; V <sub>GE</sub> = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		2,1	2,5	V
		T <sub>j</sub> = 150 °C <sub>chiplev.</sub>		2,4	2,5	V
V <sub>F0</sub>		T <sub>j</sub> = 25 °C		1,3	1,5	V
		T <sub>j</sub> = 150 °C		0,9	1,1	V
r <sub>F</sub>		T <sub>j</sub> = 25 °C		12	13,3	V
		T <sub>j</sub> = 150 °C		16	17,3	V
I <sub>RRM</sub>	I <sub>F</sub> = 75 A	T <sub>j</sub> = 150 °C		45		A
Q <sub>rr</sub>	di/dt = 2000 A/μs			10		μC
E <sub>rr</sub>	V <sub>CC</sub> = 600V			3		mJ
R <sub>th(j-s)FD</sub>	per diode			0,97		K/W
M <sub>s</sub>	to heat sink				2,5	Nm
w				30		g
Temperature sensor						
R <sub>100</sub>	T <sub>s</sub> =100°C (R <sub>25</sub> =5kΩ)			493±5%		Ω

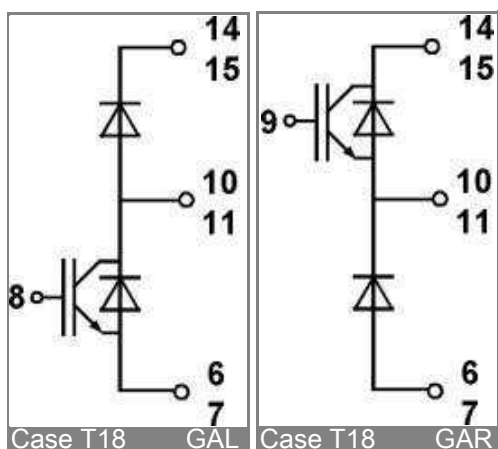








Case T18 (Suggested hole diameter for the solder pins and mounting plastic pins: 2mm)



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

#### \*IMPORTANT INFORMATION AND WARNINGS

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